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Jimmy Hsu, Sam Yang, Wei-Da Guo, Renee Lee, and Tung-Yang Chen – Himax Technologies, Inc.	
Thermal Design of a 16W LED Bulb Based on Thermal Analysis of a 4W LED Bulb	1906
Xiaobing Luo, Zhangming Mao, and Sheng Liu – Huazhong University of Science & Technology	
Comprehensive Design Guidance for PTH Via Stub in Board-Level High Speed Differential Interconnects	1912
Jaemin Shin and Timothy Michalka – QUALCOMM Incorporated	
Modeling and Measurements of Lead Titanate Acoustic Transducers for Input Impedance Matching Development	1920
Kyu Tak Son and Chin C. Lee – University of California, Irvine	
Link Analysis and Design of High Speed Storage Buses in Backplane and Cabling Environments	1929
Nanju Na, Tao Wang, Scot Baumgartner, Rohan Mandrekar, and Yaping Zhou – IBM Corporation	
Yield Modeling of 3D Integrated Wafer Scale Assemblies	1935
David V. Campbell – Sandia National Laboratories	
Interfacial Fracture Parameters of Silicon-to-Molding Compound	1939
G. Schlottig – Infineon Technologies AG, Fraunhofer IZM, Delft University of Technology; I. Maus – AMIC Angewandte Micro-Messtechnik GmbH; H. Walter – Fraunhofer IZM; K.M.B. Jansen and L.J. Ernst – Delft University of Technology; H. Pape – Infineon Technologies AG; B. Wunderle – Fraunhofer IZM, Chemnitz University of Technology	
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Comparison of Advanced PoP Package Configurations	1946
Hamid Eslampour, SeongMin Lee, SeongWon Park, TaeKeun Lee, InSang Yoon, and YoungChul Kim – STATS ChipPAC, Inc.	
Nondestructive Evaluation of the Delamination of Fine Bumps in Three-Dimensionally Stacked Flip Chip Structures	1951
Yuhki Sato, Naokazu Murata, Kinji Tamakawa, Ken Suzuki, and Hideo Miura – Tohoku University	
Development of a New Package-on-Package (PoP) Structure for Next-Generation Portable Electronics	1957
Peng Sun, Vincent Leung, Debbie Yang, Robin Lou, Daniel Shi, and Tom Chung – ASTRI	
High Speed Touch Screen Panels (TSPs) Assembly Using Anisotropic Conductive Adhesives (ACAs) Vertical Ultrasonic Bonding Method	1964
Seung-Ho Kim, Kiwon Lee, and Kyung-Wook Paik – KAIST	
Study of Warpage Characteristics of Molded Stacked-Die MCP Using Shadow Moiré and Micro Moiré Techniques	1968
David W. Wang, Hsiang-Ming Huang, Shu-Ching Ho, An-Hong Liu, and De-Shin Liu – ChipMOS Technologies, Inc.	

Electrical Characterization of Embedded Polymer/Ceramic Capacitors from 500 MHz to 12 GHz	1974
Ann Trippe, Swapan K. Bhattacharya, and John Papapolymerou – Georgia Institute of Technology; Jason Ferguson – NSWC Crane	
Fabrication of a Switch Module by Embedding Chip Capacitors and an Active IC in Organic Substrate	1980
Jong-In Ryu, Jong-Won Moon, Se-Hoon Park, Dongsu Kim, Jun-Chul Kim, and Jong-Chul Park – Korea Electronics Technology Institute	
Generalized Efficiency Measure for an Above-IC Multifilar Transformer Applied to Multiport Integrated Passive Devices	1986
C.H. Chen, C.H. Huang, and T.S. Horng – National Sun Yat-Sen University; J.Y. Li and C.C. Chen – Industrial Technology Research Institute (ITRI); C.C. Wang, C.T. Chiu, and C.P. Hung – Advanced Semiconductor Engineering, Inc.	
Novel Low Loss Thin Film Materials For Wireless 60 GHz Applications	1990
Aida L. Vera López, Swapan K. Bhattacharya, Carlos A. Donado Morcillo, and John Papapolymerou – Georgia Institute of Technology; Debabani Choudhury – Intel Corporation; Allen Horn – Rogers Corporation	
RF MEMS Wafer-Level Packaging Using Solder Paste by Via Filling Process	1996
Sunghae Jung, Myunglae Lee, and Jong-Tae Moon – Electronics and Telecommunications Research Institute	
A Compact 4x10-Gb/s CWDM ROSA Module for 40G Ethernet Optical Transceiver	2001
Sae-Kyoung Kang, Joon Ki Lee, Jyung Chan Lee, and Kwangjoon Kim – Electronics and Telecommunications Research Institute	
An Electrical Design and Fabrication of a 12-Channel Optical Transceiver with SiP Packaging Technology	2006
Wei Gao, Zhihua Li, Jian Song, Xu Zhang, Feng Chen, Fengman Liu, Yunyan Zhou, Jun Li, Haifei Xiang, Jing Zhou, Shuhua Liu, Yu Wang, Qidong Wan, Baoxia Li, Zhan Shi, Liqiang Cao, and Lixi Wan – Institute of Microelectronics, Chinese Academy of Sciences	
Organic Optical Waveguide Fabrication in a Manufacturing Environment	2012
Benson Chan, How Lin, Chase Carver, Jianzhuang Huang, and Jessie Berry – Endicott Interconnect Technologies, Inc.	
Joint Properties of Solder Capped Copper Pillars for 3D Packaging	2019
Yoon-Ki Sa, Sehoon Yoo, Yue-Seon Shin, Min-Kyu Han, and Chang-Woo Lee – Korea Institute of Industrial Technology	
High Rejection Low-Pass-Filter Design Using Integrated Passive Device Technology for Chip Scale Module Package	2025
Yong-Taek Lee, Kai Liu, Hyun-Tai Kim, Gwang Kim, and Billy Ahn – STATSChipPAC, Inc.; Robert Frye – RF Design Consulting	
New Methodology for Enhancing Electrical Conductivity and Strength of Copper Alloy Using Combined Structure	2031
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Fabrication and Characterization of Embedded Active and Passive Device for Wireless Application	2035
Se-Hoon Park, Jong-In Ryu, Jun Chul Kim, Nam Kee Kang, and Jong Chul Park – Korea Electronics Technology Institute; Young-Ho Kim – Hanyang University	
Analysis of the Laser Transmission Rate of Silicon (Si) Applied to Flip-Chip Bonding	2042
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